# UT54ACTS541E

#### **Features**

- Three-state outputs drive bus lines or buffer memory address registers
- 0.6μm CRH CMOS Process
  - Latchup immune
- · High speed
- Low power consumption
- Wide operating power supply from 3.0V to 5.5V
- Available QML Q or V processes
- 20-lead flatpack

### **Description**

The UT54ACTS541E is a non-inverting octal buffer and line driver which improves the performance and density of three-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The device is characterized over full HiRel temperature range of -55°C to +125°C.

### **Pinout**

1G       1       20       VD         A1       2       19       2G         A2       3       18       Y1         A3       4       17       Y2         A4       5       16       Y3	
A2 3 18 Y1 A3 4 17 Y2 A4 5 16 Y3	DD
A3 4 17 Y2 A4 5 16 Y3	3
5 16 Y3	1
A7	2
	3
A5 6 15 Y4	4
A6 7 14 Y5	5
A7 8 13 Y6	3
A8 9 12 Y7	7
V <sub>SS</sub> 10 11 Y8	3

20-Lead Flatpack Top View

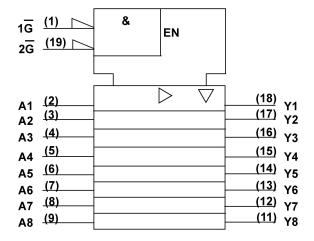
### **Function Table**

Inputs			Output
1G	<del>2</del> G	An	Yn
L	L	L	L
L	L	Н	Н
Н	X	X	Z
X	Н	X	Z



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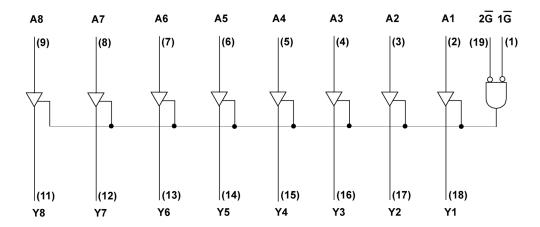
## **Logic Symbol**



#### Note:

1) Logic symbol in accordance with ANSI/IEEE std 91-1984 and IEC Publication 617-12.

### **Logic Diagram**



## Operational Environment <sup>1</sup>

Parameter	Limit	Units
Total Dose	1.0E6	rads(Si)
SEU Threshold <sup>2</sup>	80	MeV-cm <sup>2</sup> /mg
SEL Threshold	120	MeV-cm <sup>2</sup> /mg
Neutron Fluence	1.0E14	n/cm²

- 1) Logic will not latchup during radiation exposure within the limits defined in the table.
- 2) Device storage elements are immune to SEU affects.



# UT54ACTS541E

## Absolute Maximum Ratings <sup>1</sup>

Symbol	Parameter	Limit	Units
$V_{DD}$	Supply voltage	-0.3 to 7.0	V
$V_{\rm I/O}$	Voltage any pin	3 to V <sub>DD</sub> +.3	V
T <sub>STG</sub>	Storage Temperature range	-65 to +150	°
T <sub>J</sub>	Maximum junction temperature	+175	°C
T <sub>LS</sub>	Lead temperature (soldering 5 seconds)	+300	°C
$\Theta_{\sf JC}$	$\Theta_{ exttt{JC}}$ Thermal resistance junction to case		°C/W
$I_{\mathrm{I}}$	I <sub>I</sub> DC input current		mA
$P_D$	Maximum power dissipation	1	W

#### Note:

1) Stresses outside the listed absolute maximum ratings may cause permanent damage to the device. This is a stress rating only, functional operation of the device at these or any other condition beyond limits indicated in the operational sections is not recommended. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### **Recommended Operating Conditions**

Symbol	Parameter	Limit	Units
$V_{DD}$	Supply voltage	3.0 to 5.5	V
$V_{\mathrm{IN}}$	Input voltage any pin	$0$ to $V_{\text{DD}}$	V
T <sub>C</sub>	Temperature range	-55 to + 125	°C



## UT54ACTS541E

### DC Electrical Characteristics for the UT54ACTS541E 7

 $(V_{DD} = 3.0V \text{ to } 5.5V; V_{SS} = 0V^6, -55^{\circ}C < T_C < +125^{\circ}C)$ 

Symbol	Description	Condition	VDD	MIN	MAX	Unit	
V <sub>IL</sub> Low-level input voltage	Low level input voltage 1		3.0V		0.8	V	
	Low-level input voltage		5.5V		0.8	, v	
	V 18 1 1 1 1 1 1 1		3.0V	2.0		V	
$V_{\mathrm{IH}}$	High-level input voltage <sup>1</sup>		5.5V	2.75		, v	
$I_{IN}$	Input leakage current	$V_{IN} = V_{DD}$ or $V_{SS}$	5.5V	-1	1	μΑ	
V	Low-level output voltage <sup>3</sup>	$I_{OL} = 8mA$	3.0V		0.4	V	
$V_{OL}$	Low-level output voltage	$I_{OL} = 12mA$	4.5V		0.4	V	
V	High level autout valle = - 3	$I_{OH} = -8mA$	3.0V	2.4		V	
V <sub>OH</sub>	High-level output voltage <sup>3</sup>	I <sub>OH</sub> = -12mA	4.5V	3.15		V	
т	Short-circuit output current <sup>2, 4</sup>	$V_{O} = V_{DD}$ and $V_{SS}$	3.0V	-150	150	- mA	
$I_{OS}$			5.5V	-300	300		
т	Low level output current 10	$V_{IN} = V_{DD}$ or $V_{SS}$	3.0V	8		m A	
$I_{OL}$	Low level output current	$V_{OL} = 0.4V$	5.5V	12		- mA	
т	High level autout august 10	$I_{OH}$ High level output current $^{10}$ $V_{IN} = V_{IN}$	$V_{IN} = V_{DD}$ or $V_{SS}$	3.0V		-8	mA
${ m I}_{\sf OH}$	riigir ievei output current	$V_{OH} = V_{DD}$ -0.4V	5.5V		-12	IIIA	
D .	Daniel diameter 2.80	$C_L = 50pF$	5.5V		2.1	mW/	
P <sub>total</sub>	Power dissipation <sup>2, 8, 9</sup>	CL — 30pr	3.0V		0.84	MHz	
$I_{DDQ}$	Quiescent Supply Current	$V_{IN} = V_{DD}$ or $V_{SS}$	5.5V		10	μΑ	
$\Delta I_{ extsf{DDQ}}$	Quiescent Supply Current Delta	For input under test $V_{IN} = V_{DD} - 2.1V$ For all other inputs $V_{IN} = V_{DD} \text{ or } V_{SS}$	5.5V		1.6	mA	
$C_{IN}$	Input capacitance <sup>5</sup>	f= 1MHz	0V		15	pF	
C <sub>OUT</sub>	Output capacitance <sup>5</sup>	f = 1MHz	0V		15	pF	

- 1) Functional tests are conducted in accordance with MIL-STD-883 with the following input test conditions:  $V_{IH} = V_{IH} (min) + 20\%$ , 0%;  $V_{IL} = V_{IL} (max) + 0\%$ , 50%, as specified herein, for TTL, CMOS, or Schmitt compatible inputs. Devices may be tested using any input voltage within the above specified range, but are guaranteed to  $V_{IH} (min)$  and  $V_{IL} (max)$ .
- 2) Supplied as a design limit but not guaranteed or tested.
- 3) Per MIL-PRF-38535, for current density ≤5.0E5 amps/cm², the maximum product of load capacitance (per output buffer) times frequency should not exceed 3,765pF/MHz.
- 4) Not more than one output may be shorted at a time for maximum duration of one second.
- 5) Capacitance measured for initial qualification and when design changes may affect the value. Capacitance is measured between the designated terminal and V<sub>SS</sub> at frequency of 1MHz and a signal amplitude of 50mV rms maximum.
- 6) Maximum allowable relative shift equals 50mV.
- 7) All specifications valid for radiation dose ≤ 1E6 rads(Si) per MIL-STD-883 Method 1019 Condition A and section 3.11.2.
- 8) Power does not include power contribution of any TTL output sink current.
- 9) Power dissipation specified per switching output.
- 10) This value is guaranteed based on characterization data, but not tested.



# UT54ACTS541E

### AC Electrical Characteristics for the UT54ACTS541E <sup>2</sup>

 $(V_{DD} = 3.0V \text{ to } 5.5V; V_{SS} = 0V^{-1}, -55^{\circ}C < T_{C} < +125^{\circ}C)$ 

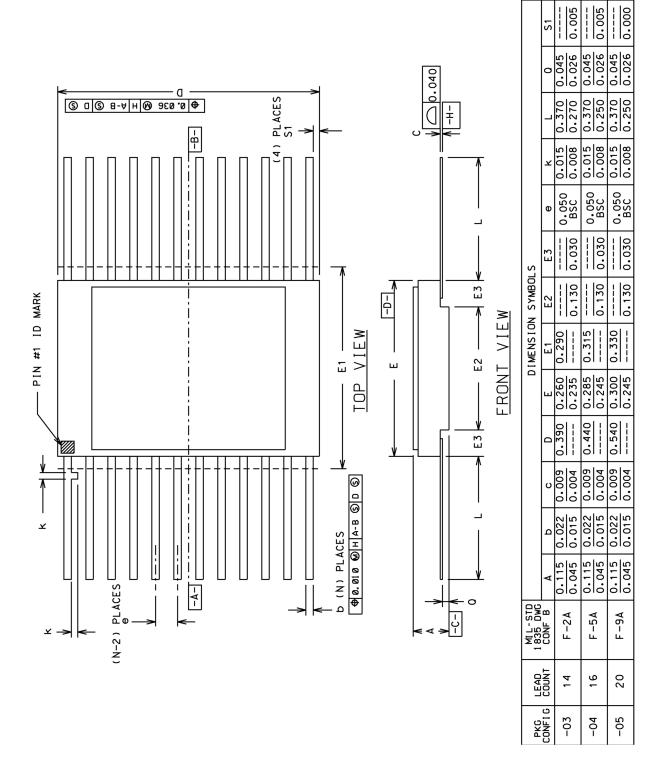
Symbol	Parameter	Condition	<b>V</b> <sub>DD</sub>	Minimum	Maximum	Unit
	As to Ve	C = 20nE	3.0V & 3.6V	1	11	ns
		$C_L = 30pF$	4.5V & 5.5V	1	8	
t <sub>PLH</sub>	An to Yn	C	3.0V & 3.6V	1	15	
		$C_L = 50pF$	4.5V & 5.5V	1	11	ns
		$C_L = 30pF$	3.0V & 3.6V	1	14	nc
+	An to Yn	$C_L = 30pr$	4.5V & 5.5V	1	10	ns
t <sub>PHL</sub>	All to fil	C - F0pF	3.0V & 3.6V	1	18	nc
		$C_L = 50pF$	4.5V & 5.5V	1	14	ns
		$C_L = 30pF$	3.0V & 3.6V	2	15	nc
	t <sub>PZH</sub> G low to Yn active	$C_L = 30pr$	4.5V & 5.5V	2	11	ns
ЧРZН		$C_L = 50pF$	3.0V & 3.6V	2	19	- ns
		$C_L = SUPF$	4.5V & 5.5V	2	15	
	G low to Yn active	$C_L = 30pF$	3.0V & 3.6V	2	14	ns
		CL = 30pr	4.5V & 5.5V	2	10	115
t <sub>PZL</sub>		$C_L = 50pF$	3.0V & 3.6V	2	18	nc
		CL = 30pr	4.5V & 5.5V	2	14	ns
	5	$C_L = 30pF$	3.0V & 3.6V	1	13	ns
_		CL = SUPP	4.5V & 5.5V	1	9	ns
t <sub>PHZ</sub>	G low to Yn active	$C_L = 50pF$	3.0V & 3.6V	2	17	nc
		C <sub>L</sub> = 30pr	4.5V & 5.5V	2	13	ns
		C <sub>L</sub> = 30pF	3.0V & 3.6V	2	12	no
_	<u>-</u>		4.5V & 5.5V	2	8	ns
t <sub>PLZ</sub>	G low to Yn active	C 50=5	3.0V & 3.6V	2	16	
		$C_L = 50pF$	4.5V & 5.5V	2	12	ns

- 1) Maximum allowable relative shift equals 50mV.
- 2) All specifications valid for radiation dose ≤ 1E6 rads(Si) per MIL-STD-883 Method 1019 Condition A and section 3.11.2.



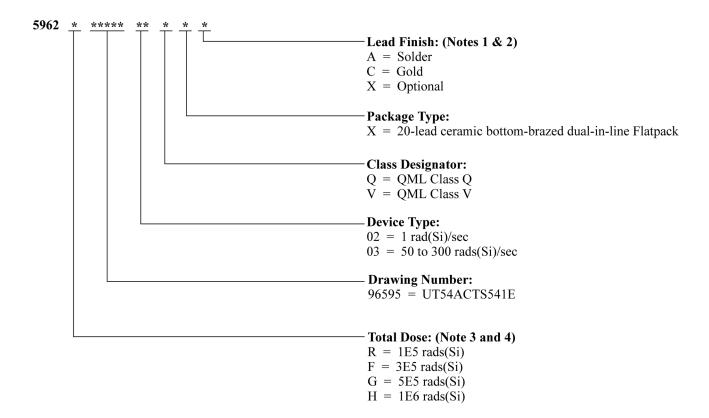
# UT54ACTS541E

## **Packaging**



# UT54ACTS541E

### Ordering Information: UT54ACTS541E: SMD



- 1) Lead finish (A,C, or X) must be specified.
- 2) If an "X" is specified when ordering, part marking will match the lead finish and will be either "A" (solder) or "C" (gold).
- 3) Total dose radiation must be specified when ordering. QML Q and QML V not available without radiation hardening. For prototype inquiries, contact factory.
- 4) Device type 02 is only offered with a TID tolerance guarantee of 3E5 rads(Si) or 1E6 rads(Si) and is tested in accordance with MIL-STD-883 Test Method 1019 Condition A and section 3.11.2. Device type 03 is only offered with a TID tolerance guarantee of 1E5 rads(Si), 3E5 rads(Si), and 5E5 rads(Si), and is tested in accordance with MIL-STD-883 Test Method 1019 Condition A.



# UT54ACTS541E

#### **Datasheet Definitions**

Datasneet Dermitions		
	DEFINITION	
Advanced Datasheet	CAES reserves the right to make changes to any products and services described herein at any time without notice. The product is still in the development stage and the datasheet <b>is subject to change</b> . Specifications can be <b>TBD</b> and the part package and pinout are <b>not final</b> .	
Preliminary Datasheet	CAES reserves the right to make changes to any products and services described herein at any time without notice. The product is in the characterization stage and prototypes are available.	
Datasheet	Product is in production and any changes to the product and services described herein will follow a formal customer notification process for form, fit or function changes.	

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